Lateral power MOSFET having metal strap layer to reduce distributed resistance and method of fabricating the same

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Inventor(s): WILLIAMS RICHARD K (US)

Applicant(s): SILICONIX INC (US)

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Abstract

To reduce the distributed resistance in an integrated circuit die, a relatively thick metal strap layer is deposited on a bus or other conductive path in the top metal layer. The metal strap layer is formed by etching a longitudinal channel in the passivation layer over the bus and plating a thick metal layer, preferably nickel, in the channel. The metal strap layer dramatically reduces the resistance of the bus.